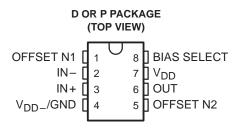
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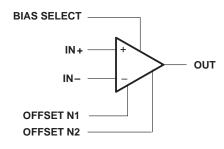
- Wide Range of Supply Voltages 1.4 V to 16 V
- True Single-Supply Operation
- Common-Mode Input Voltage Range Includes the Negative Rail
- Low Noise . . . 30 nV/√Hz Typ at 1 kHz (High Bias)
- ESD Protection Exceeds 2000 V Per MIL-STD-833C, Method 3015.1

description

The TLC251C, TLC251AC, and TLC251BC are low-cost, low-power programmable operational amplifiers designed to operate with single or dual supplies. Unlike traditional metal-gate CMOS operational amplifiers, these devices utilize Texas Instruments silicon-gate LinCMOS™ process, giving them stable input offset voltages without sacrificing the advantages of metal-gate CMOS.



symbol



This series of parts is available in selected grades of input offset voltage and can be nulled with one external potentiometer. Because the input common-mode range extends to the negative rail and the power consumption is extremely low, this family is ideally suited for battery-powered or energy-conserving applications. A bias-select pin can be used to program one of three ac performance and power-dissipation levels to suit the application. The series features operation down to a 1.4-V supply and is stable at unity gain.

These devices have internal electrostatic-discharge (ESD) protection circuits that prevent catastrophic failures at voltages up to 2000 V as tested under MIL-STD-883C, Method 3015.1. However, care should be exercised in handling these devices as exposure to ESD may result in a degradation of the device parametric performance.

Because of the extremely high input impedance and low input bias and offset currents, applications for the TLC251C series include many areas that have previously been limited to BIFET and NFET product types. Any circuit using high-impedance elements and requiring small offset errors is a good candidate for cost-effective use of these devices. Many features associated with bipolar technology are available with LinCMOSTM operational amplifiers without the power penalties of traditional bipolar devices. Remote and inaccessible equipment applications are possible using the low-voltage and low-power capabilities of the TLC251C series.

In addition, by driving the bias-select input with a logic signal from a microprocessor, these operational amplifiers can have software-controlled performance and power consumption. The TLC251C series is well suited to solve the difficult problems associated with single battery and solar cell-powered applications.

The TLC251C series is characterized for operation from 0°C to 70°C.

AVAILABLE OPTIONS

	V may	PACKAGEI	DEVICES	CHIP FORM
TA	V _{IO} max AT 25°C	SMALL OUTLINE (D)	PLASTIC DIP (P)	(Y)
	10 mV	TLC251CD	TLC251CP	TLC251Y
0°C to 70°C	5 mV	TLC251ACD	TLC251ACP	_
	2 mV	TLC251BCD	TLC251BCP	-

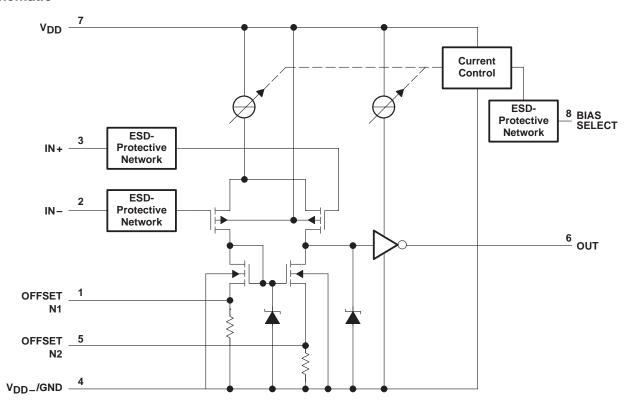
The D package is available taped and reeled. Add the suffix R to the device type (e.g., TLC251CDR). Chips are tested at 25°C.

LinCMOS is a trademark of Texas Instruments Incorporated.



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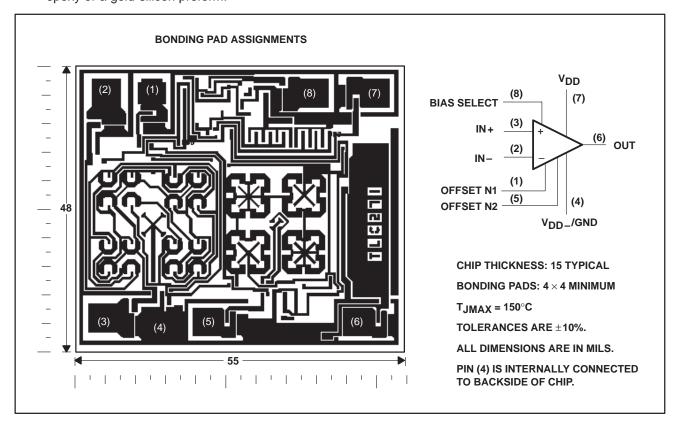
schematic



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TLC251Y chip information

These chips, properly assembled, display characteristics similar to the TLC251C. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage, V _{DD} (see Note 1)	18 V
Differential input voltage, V _{ID} (see Note 2)	±18 V
Input voltage range, V _I (any input)	
Duration of short circuit at (or below) 25°C free-air temperature (see Note 3)	unlimited
Continuous total dissipation	. See Dissipation Rating Table
Operating free-air temperature range, T _A	0°C to 70°C
Storage temperature range	65°C to 150°C
Lead temperature 1.6 mm (1/16 inch) from case for 10 seconds	260°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, except differential voltages, are with respect to V_{DD}_/GND.
 - 2. Differential voltages are at IN+ with respect to IN-.
 - 3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure the maximum dissipation rating is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{\scriptsize A}} \leq 25^{\circ}\mbox{\scriptsize C}$ POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING
D	725 mW	5.8 mW/°C	464 mW
Р	1000 mW	8.0 mW/°C	640 mW

recommended operating conditions

		MI	N MAX	UNIT
Supply voltage, V _{DD}		1.	4 16	V
	V _{DD} = 1.4 V		0 0.2	
Common mode input voltage. Vice	V _{DD} = 5 V	-0.	2 4] ,
Common-mode input voltage, V _{IC}	V _{DD} = 10 V	-0.	2 9]
	V _{DD} = 16 V	-0.	2 14	1
Operating free-air temperature, TA			0 70	°C
Bias-select voltage			See Applic Informat	



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HIGH-BIAS MODE

electrical characteristics at specified free-air temperature

					Т	LC251C	, TLC25	1AC, TL	C251BC		
	PARAMETER		TEST CONDITIONS	T _A †	V	DD = 5 \	<i>'</i>	٧٢	OD = 10	V	UNIT
			CONDITIONS		MIN	TYP	MAX	MIN	TYP	MAX	
		TLC251C		25°C		1.1	10		1.1	10	
		TLGZ51C	V _O = 1.4 V,	Full range			12			12	
1/10	Input offeet voltage	TLC251AC	$V_{IC} = 0 V$	25°C		0.9	5		0.9	5	mV
VIO	Input offset voltage	TLGZSTAC	$R_S = 50 \Omega$,	Full range			6.5			6.5	IIIV
		TLC251BC	$R_L = 10 \text{ k}\Omega$	25°C		0.34	2		0.39	2	
		TLC25TBC		Full range			3			3	
ανιο	Average temperature input offset voltage	coefficient of		25°C to 70°C		1.8			2		μV/°C
lio.	Input offset current (s	oo Noto 4)	$V_O = V_{DD}/2$,	25°C		0.1			0.1		pА
lio	input onset current (s	ee Note 4)	$V_{IC} = V_{DD}/2$	70°C		7	300		7	300	PΑ
I	Input bias current (se	o Noto 4)	$V_O = V_{DD}/2$,	25°C		0.6			0.7		- A
IB	input bias current (se	e Note 4)	$V_{IC} = V_{DD}/2$	70°C		40	600		50	600	pА
					-0.2	-0.3		-0.2	-0.3		
				25°C	to 4	to 4.2		to 9	to 9.2		V
VICR	Common-mode input range (see Note 5)	voltage			-0.2	4.2		-0.2	9.2		
	range (see Note 5)			Full range	-0.2 to			-0.2 to			V
				Ŭ	3.5			8.5			
			100	25°C	3.2	3.8		8	8.5		
Vон	High-level output volta	age	$V_{ID} = 100 \text{ mV},$ $R_{I} = 10 \text{ k}\Omega$	0°C	3	3.8		7.8	8.5		V
			10 101	70°C	3	3.8		7.8	8.4		
			400	25°C		0	50		0	50	
VOL	Low-level output volta	ige	$V_{ID} = -100 \text{ mV},$ $I_{OI} = 0$	0°C		0	50		0	50	mV
			IOL = 0	70°C		0	50		0	50	
			D 4010	25°C	5	23		10	36		
A _{VD}	Large-signal differenti amplification	iai voitage	R_L = 10 kΩ, See Note 6	0°C	4	27		7.5	42		V/mV
	атритоалог		000 11010 0	70°C	4	20		7.5	32		
				25°C	65	80		65	85		
CMRR	Common-mode reject	tion ratio	V _{IC} = V _{ICR} min	0°C	60	84		60	88		dB
				70°C	60	85		60	88		
				25°C	65	95		65	95		
ksvr	Supply-voltage rejecti (ΔV _{DD} /ΔV _{IO})	on ratio	$V_{DD} = 5 \text{ V to } 10 \text{ V},$ $V_{O} = 1.4 \text{ V}$	0°C	60	94		60	94		dB
	(A V DD/ A V IO)		VU = 1.4 V	70°C	60	96		60	96		
I _I (SEL)	Input current (BIAS S	ELECT)	V _{I(SEL)} = 0	25°C		-1.4			-1.9		μΑ
			$V_O = V_{DD}/2$,	25°C		675	1600		950	2000	
IDD	Supply current		$V_{IC} = V_{DD}/2$,	0°C		775	1800		1125	2200	μΑ
<u> </u>			No load	70°C		575	1300		750	1700	

†Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

- 5. This range also applies to each input individually.
- 6. At $V_{DD} = 5 \text{ V}$, $V_{O} = 0.25 \text{ V}$ to 2 V; at $V_{DD} = 10 \text{ V}$, $V_{O} = 1 \text{ V}$ to 6 V.



HIGH-BIAS MODE

operating characteristics, $V_{DD} = 5 \text{ V}$

	PARAMETER	т	EST CONDITION	ONS	TA	TLC251C, TLC251AC, TLC251BC			UNIT
						MIN	TYP	MAX	
					25°C		3.6		
				V _{I(PP)} = 1 V	0°C		4		
SR	Slew rate at unity gain	$R_L = 10 \text{ k}\Omega$,	C. = 20 pE		70°C		3		V/μs
J	Siew rate at unity gain		CL = 20 pr		25°C		2.9		ν/μ5
				V _{I(PP)} = 2.5 V	0°C		3.1		
					70°C		2.5		
٧n	Equivalent input noise voltage	f = 1 kHz,	$R_S = 20 \Omega$		25°C		25		nV/√ Hz
					25°C		320		
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$	$C_L = 20 pF$,	$R_L = 10 \text{ k}\Omega$	0°C		340		kHz
					70°C		260		
					25°C		1.7		
В1	Unity-gain bandwidth	$V_{I} = 10 \text{ mV},$	$C_{L} = 20 pF$		0°C		2		MHz
					70°C		1.3		
	-			-	25°C		46°		
φm	Phase margin	V _I = 10 mV,	$f = B_1$,	$C_L = 20 pF$	0°C		47°		
					70°C		44°		

operating characteristics, $V_{DD} = 10 \text{ V}$

	PARAMETER	1	EST CONDITION	ONS	TA	TLC251C, TLC251AC, TLC251BC			UNIT
						MIN	TYP	MAX	
					25°C		5.3		
				V _{I(PP)} = 1 V	0°C		5.9		
SR	Slow rate at unity gain	$R_L = 10 \text{ k}\Omega$	C 20 pE		70°C		4.3		\//uc
J SK	Slew rate at unity gain	$R = 10 \text{ K}_{2}$	C[= 20 pr		25°C		4.6		V/μs
				V _{I(PP)} = 5.5 V	0°C		5.1		
					70°C		3.8		
Vn	Equivalent input noise voltage	f = 1 kHz,	R _S = 20 Ω		25°C		25		nV/√ Hz
					25°C		200		
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$	$C_L = 20 pF$,	$R_L = 10 \text{ k}\Omega$	0°C		220		kHz
					70°C		140		
					25°C		2.2		
В1	Unity-gain bandwidth	$V_{I} = 10 \text{ mV},$	$C_{L} = 20 \text{ pF}$		0°C		2.5		MHz
					70°C		1.8		
					25°C		49°		
φm	Phase margin	V _I = 10 mV,	f = B ₁ ,	$C_L = 20 pF$	0°C		50°		
					70°C		46°		

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MEDIUM-BIAS MODE

electrical characteristics at specified free-air temperature

					Т	LC251C	, TLC25	1AC, TL	C251BC		
	PARAMETER		TEST CONDITIONS	T _A †	V	DD = 5 \	/	٧	OD = 10 \	V	UNIT
			CONDITIONS		MIN	TYP	MAX	MIN	TYP	MAX	
		TLC251C		25°C		1.1	10		1.1	10	
		11.02510	Vo = 1.4.V	Full range			12			12	
\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	lanut offeet valte as	TLC251AC	$V_{O} = 1.4 \text{ V},$ $V_{IC} = 0 \text{ V},$	25°C		0.9	5		0.9	5	\ /
VIO	Input offset voltage	TLG25TAG	$R_S = 50 \Omega$,	Full range			6.5			6.5	mV
		TLC251BC	$R_L = 10 \text{ k}\Omega$	25°C		0.34	2		0.39	2	
		TLC25TBC		Full range			3			3	
ανιο	Average temperature input offset voltage	coefficient of		25°C to 70°C		1.7			2.1		μV/°C
	Innut offeet oursent (e	on Note 4)	$V_O = V_{DD}/2$,	25°C		0.1			0.1		- ^
lio	Input offset current (s	ee Note 4)	$V_{IC} = V_{DD}/2$	70°C		7	300		7	300	pА
	Input bigg gurrent (go	a Nieta 4)	$V_O = V_{DD}/2$,	25°C		0.6			0.7		5 A
lΒ	Input bias current (se	e Note 4)	$V_{IC} = V_{DD}/2$	70°C		40	600		50	600	pА
	Common-mode input	voltage		25°C	-0.2 to 4	-0.3 to 4.2		-0.2 to 9	-0.3 to 9.2		V
VICR	range (see Note 5)			Full range	-0.2 to 3.5			-0.2 to 8.5			V
				25°C	3.2	3.9		8	8.7		
VOH	High-level output volt	age	$V_{ID} = 100 \text{ mV},$ $R_{I} = 10 \text{ k}\Omega$	0°C	3	3.9		7.8	8.7		V
				70°C	3	4		7.8	8.7		
				25°C		0	50		0	50	
VOL	Low-level output volta	age	$V_{ID} = -100 \text{ mV},$ $I_{OL} = 0$	0°C		0	50		0	50	mV
			IOL = 0	70°C		0	50		0	50	
			B 4016	25°C	25	170		25	275		
A _{VD}	Large-signal different amplification	ial voltage	R_L = 10 kΩ, See Note 6	0°C	15	200		15	320		V/mV
	ampimoation.		000 11010 0	70°C	15	140		15	230		
				25°C	65	91		65	94		
CMRR	Common-mode reject	tion ratio	V _{IC} = V _{ICR} min	0°C	60	91		60	94		dB
				70°C	60	92		60	94		
	Cumply voltage:	ion rotio	V== EV40 40 V	25°C	70	93		70	93		
ksvr	Supply-voltage reject (ΔVDD/ΔVIO)	เบา เสแบ	$V_{DD} = 5 \text{ V to } 10 \text{ V},$ $V_{O} = 1.4 \text{ V}$	0°C	60	92		60	92		dB
			Ŭ	70°C	60	94		60	94		
I(SEL)	Input current (BIAS S	ELECT)	$V_{I(SEL)} = V_{DD}/2$	25°C		-130			-160		nA
			$V_O = V_{DD}/2$,	25°C		105	280		143	300	
IDD	Supply current		V _{IC} = V _{DD} /2, No load	0°C		125	320		173	400	μΑ
			140 1080	70°C		85	220		110	280	

† Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

- 5. This range also applies to each input individually.
- 6. At $V_{DD} = 5 \text{ V}$, $V_{O} = 0.25 \text{ V}$ to 2 V; at $V_{DD} = 10 \text{ V}$, $V_{O} = 1 \text{ V}$ to 6 V.



MEDIUM-BIAS MODE

operating characteristics, $V_{DD} = 5 \text{ V}$

	PARAMETER	Т	EST CONDITIO	NS	TA	TLC251C, TLC251AC, TLC251BC			UNIT
						MIN	TYP	MAX	
					25°C		0.43		
				V _{I(PP)} = 1 V	0°C		0.46		
SR	Slow rate at unity gain	R _L = 100 kΩ,	C 20 pE		70°C		0.36		\//ua
J SK	Slew rate at unity gain	K[= 100 K22,	C[= 20 pr		25°C		0.40		V/μs
				V _{I(PP)} = 2.5 V	0°C		0.43		
					70°C		0.34		
Vn	Equivalent input noise voltage	f = 1 kHz,	$R_S = 20 \Omega$		25°C		32		nV/√ Hz
					25°C		55		
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$	$C_L = 20 pF$,	R _L = 100 kΩ	0°C		60		kHz
					70°C		50		
					25°C		525		
В1	Unity-gain bandwidth	$V_{I} = 10 \text{ mV},$	$C_{L} = 20 pF$		0°C		600		kHz
					70°C		400		
					25°C		40°		
φm	Phase margin	V _I = 10 mV,	$f = B_1$,	$C_L = 20 pF$	0°C		41°		
					70°C		39°		

operating characteristics, $V_{DD} = 10 \text{ V}$

	PARAMETER	т	EST CONDITIO	ONS	TA	TLC251C, TLC251AC, TLC251BC			UNIT
						MIN	TYP	MAX	
					25°C		0.62		
				V _{I(PP)} = 1 V	0°C		0.67		
SR	Slew rate at unity gain	R _L = 100 kΩ,	C ₁ = 20 pE		70°C		0.51		\//ue
JSK	Siew rate at unity gain	K_ = 100 KS2,	CL = 20 pr		25°C		0.56		V/μs
				$V_{I(PP)} = 5.5 V$	0°C		0.61		
					70°C		0.46		
٧n	Equivalent input noise voltage	f = 1 kHz,	$R_S = 20 \Omega$		25°C		32		nV/√ Hz
					25°C		35		
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$	$C_L = 20 pF$,	$R_L = 100 \text{ k}\Omega$	0°C		40		kHz
					70°C		30		
					25°C		635		
B ₁	Unity-gain bandwidth	$V_{ } = 10 \text{ mV},$	$C_L = 20 pF$		0°C		710		kHz
					70°C		510		
					25°C		43°		
φm	Phase margin	V _I = 10 mV,	$f = B_1$,	$C_L = 20 pF$	0°C		44°		
					70°C		42°		

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LOW-BIAS MODE

electrical characteristics at specified free-air temperature

					Т	LC251C	, TLC25	1AC, TL	C251BC		
	PARAMETER		TEST CONDITIONS	T _A †	V	DD = 5 \	/	٧	OD = 10	V	UNIT
			CONDITIONS		MIN	TYP	MAX	MIN	TYP	MAX	
		TLC251C		25°C		1.1	10		1.1	10	
		11.02510	Vo = 1.4 V	Full range			12			12	
\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	lanut offeet valte as	TLC251AC	V _O = 1.4 V, V _{IC} = 0 V,	25°C		0.9	5		0.9	5	\/
VIO	Input offset voltage	TLC251AC	$R_S = 50 \Omega$,	Full range		•	6.5			6.5	mV
		TI COE4DC	$R_L = 10 M\Omega$	25°C		0.24	2		0.26	2	
		TLC251BC		Full range			3			3	
ανιο	Average temperature input offset voltage	coefficient of		25°C to 70°C		1.1			1		μV/°C
1	Innut offeet europt (e	on Note 4)	$V_O = V_{DD}/2$,	25°C		0.1			0.1		- ^
lio	Input offset current (s	ee Note 4)	$V_{IC} = V_{DD}/2$	70°C		7	300		7	300	pА
	Input bigg gurrent (go	a Nieta 4)	$V_O = V_{DD}/2$,	25°C		0.6			0.7		
lΒ	Input bias current (se	e Note 4)	$V_{IC} = V_{DD}/2$	70°C		40	600		50	600	pА
	Common-mode input	voltage		25°C	-0.2 to 4	-0.3 to 4.2		-0.2 to 9	-0.3 to 9.2		V
VICR	range (see Note 5)			Full range	-0.2 to 3.5			-0.2 to 8.5			V
				25°C	3.2	4.1		8	8.9		
∨он	High-level output volt	age	$V_{ID} = 100 \text{ mV},$ $R_L = 1 \text{ M}\Omega$	0°C	3	4.1		7.8	8.9		V
				70°C	3	4.2		7.8	8.9		
				25°C		0	50		0	50	
VOL	Low-level output volta	age	$V_{ID} = -100 \text{ mV},$ $I_{OL} = 0$	0°C		0	50		0	50	mV
			IOL = 0	70°C		0	50		0	50	
			D 4110	25°C	50	520		50	870		
A _{VD}	Large-signal different amplification	ial voltage	R_L = 1 MΩ, See Note 6	0°C	50	700		50	1030		V/mV
	ampimoation.		000 11010 0	70°C	50	380		50	660		
				25°C	65	94		65	97		
CMRR	Common-mode reject	tion ratio	V _{IC} = V _{ICR} min	0°C	60	95		60	97		dB
				70°C	60	95		60	97		
	Cumply voltage:	ion rotio	V== EV40 40 V	25°C	70	97		70	97		
ksvr	Supply-voltage reject (ΔVDD/ΔVIO)	וטוז ומנוס	$V_{DD} = 5 \text{ V to } 10 \text{ V},$ $V_{O} = 1.4 \text{ V}$	0°C	60	97		60	97		dB
	. 55 10/			70°C	60	98		60	98		
I(SEL)	Input current (BIAS S	ELECT)	V _I (SEL) = V _{DD}	25°C		65			95		nA
			$V_O = V_{DD}/2$,	25°C		10	17		14	23	
IDD	Supply current		V _{IC} = V _{DD} /2,	0°C		12	21		18	33	μΑ
			No load	70°C		8	14		11	20	

† Full range is 0°C to 70°C.

NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically.

- 5. This range also applies to each input individually.
- 6. At $V_{DD} = 5 \text{ V}$, $V_{O} = 0.25 \text{ V}$ to 2 V; at $V_{DD} = 10 \text{ V}$, $V_{O} = 1 \text{ V}$ to 6 V.



LOW-BIAS MODE

operating characteristics, $V_{DD} = 5 \text{ V}$

	PARAMETER	т	EST CONDITIO	ONS	TA	TLC251C, TLC251AC, TLC251BC			UNIT
						MIN	TYP	MAX	
					25°C		0.03		
				V _{I(PP)} = 1 V	0°C		0.04		
SR	Slow rate at unity gain	B. = 1 MO	C 20 pE		70°C		0.03		\//ua
SK	Slew rate at unity gain	$R_L = 1 M\Omega$,	$C_L = 20 pF$		25°C		0.03		V/μs
				V _{I(PP)} = 2.5 V	0°C		0.03		
					70°C		0.02		
٧n	Equivalent input noise voltage	f = 1 kHz,	$R_S = 20 \Omega$		25°C		68		nV/√Hz
					25°C		5		
Вом	Maximum output-swing bandwidth	$V_O = V_{OH}$	$C_L = 20 pF$,	$R_L = 1 M\Omega$	0°C		6		kHz
					70°C		4.5		
					25°C		85		
B ₁	Unity-gain bandwidth	$V_{I} = 10 \text{ mV},$	$C_L = 20 pF$		0°C		100		kHz
					70°C		65		
					25°C		34°		
φm	Phase margin	V _I = 10 mV,	$f = B_1$,	$C_L = 20 pF$	0°C		36°		
					70°C		30°		

operating characteristics, $V_{DD} = 10 \text{ V}$

	PARAMETER	т	TEST CONDITIONS				TLC251C, TLC251AC, TLC251BC		
							TYP	MAX	1 1
					25°C		0.05		
				V _{I(PP)} = 1 V	0°C		0.05		
SR	Slew rate at unity gain	$R_{I} = 1 M\Omega$	C _L = 20 pF		70°C		0.04		\//ue
JSK	Siew rate at unity gain		OL = 20 pr	V _I (PP) = 5.5 V	25°C		0.04		V/μs
					0°C		0.05		
					70°C		0.04		
٧n	Equivalent input noise voltage	f = 1 kHz,	$R_S = 20 \Omega$		25°C		68		nV/√ Hz
					25°C		1		
ВОМ	Maximum output-swing bandwidth	$V_O = V_{OH}$	$C_L = 20 pF$,	$R_L = 1 M\Omega$	0°C		1.3		kHz
					70°C		0.9		
					25°C		110		
B ₁	Unity-gain bandwidth	$V_{I} = 10 \text{ mV},$	$C_L = 20 pF$		0°C		125		kHz
					70°C		90		
			<u> </u>		25°C		38°		
φm	Phase margin	$V_{I} = 10 \text{ mV},$	$f = B_1$,	$C_L = 20 pF$	0°C		40°		
					70°C		34°		

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electrical characteristics at specified free-air temperature, V_{DD} = 1.4 V

	PARAMETE	AMETER TEST CONDITIONS† TA‡		T _A ‡	BIAS	TLC251C, TLC251AC, TLC251BC			UNIT		
							MIN	TYP	MAX		
		TLC251C			25°C	Anu			10		
		1102510			Full range	Any			12		
\/.a	Input offset	TLC251AC	V _O = 0.2 V,	Pa - 50 O	25°C	Any			5	m∨	
VIO	voltage	TLC25TAC	V() = 0.2 V,	$R_S = 50 \Omega$	Full range	Ally			6.5	IIIV	
		TLC251BC			25°C	Any			2		
		TEGZSTBC			Full range	Ally			3		
αΛΙΟ	Average temp coefficient of i voltage				25°C to 70°C	Any		1		μV/°C	
lio.	Input offset cu	rront	V _O = 0.2 V		25°C	Any		1		pA	
lio	input onset cu	irrent	V() = 0.2 V		Full range	Ally			300	PΑ	
lin.	Input bias cur	ront	V _O = 0.2 V		25°C	Any		1		рA	
IB	input bias cui	lent	V() = 0.2 V		Full range	Ally			600	PΑ	
VICR	Common-mod voltage range	de input			25°C	Any	0 to 0.2			V	
Vом	Peak output v swing§	oltage	V _{ID} = 100 mV		25°C	Any	450	700		mV	
Λ	Large-signal o	lifferential	\/ 100 to 200\/	Pa - 50 O	25°C	Low		20			
AVD	voltage amplif	ication	$V_{O} = 100 \text{ to } 300 \text{ mV}, R_{S} = 9$		25 C	High		10			
CMRR	Common-mod ratio	de rejection	$R_S = 50 \Omega$, $V_{IC} = V_{ICR}$ min	$V_0 = 0.2 V$,	25°C	Any	60	77		dB	
IDD	Supply curren	+	Vo = 0.2 V	No load	25°C	Low		5	17	пΔ	
lDD	Supply current		$V_O = 0.2 V$, No load		25 C	High		150	190	μΑ	

 $[\]overline{1}$ All characteristics are measured under open-loop conditions with zero common-mode input voltage unless otherwise specified. Unless otherwise noted, an output load resistor is connected from the output to ground and has the following values: for low bias, $R_L = 1 \, M\Omega$, for medium bias, $R_L = 100 \, k\Omega$, and for high bias, $R_L = 10 \, k\Omega$.

operating characteristics, V_{DD} = 1.4 V, T_A = 25°C

	PARAMETER	TEST CONDITIONS	BIAS	TLC251C, TLC251AC, TLC251BC			UNIT	
				MIN	TYP	MAX]	
B.	Unity goin handwidth	C 100 pE	Low		12		kHz	
B ₁	Unity-gain bandwidth	C _L = 100 pF	High		12		NITZ	
SR	Clay rate at unity gain	O Firmer 4			0.001		V/μs	
J SK	Slew rate at unity gain	See Figure 1	High		0.1		ν/μ5	
	Overshoot factor	Coo Figure 1	Low		35%			
		See Figure 1	High		30%			

[‡]Full range is 0°C to 70°C.

 $[\]mbox{\S The output swings to the potential of V_{DD}_-/GND.}$

electrical characteristics, V_{DD} = 5 V, T_A = 25°C

			TLC251Y									
	PARAMETER TEST CONDITIONS		HIGH-BIAS MODE			MEDIUM-BIAS MODE			LOW-BIAS MODE			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
VIO	Input offset voltage	$V_{O} = 1.4 \text{ V},$ $V_{IC} = 0 \text{ V},$ $R_{S} = 50 \Omega,$ R_{L}^{\dagger}		1.1	10		1.1	10		1.1	10	mV
ανιο	Average temperature coefficient of input offset voltage			1.8			1.7			1.1		μV/°C
I _{IO}	Input offset current (see Note 4)	$V_O = V_{DD}/2,$ $V_{IC} = V_{DD}/2$		0.1			0.1			0.1		pA
I _{IB}	Input bias current (see Note 4)	$V_O = V_{DD}/2,$ $V_{IC} = V_{DD}/2$		0.6			0.6			0.6		рА
VICR	Common-mode input voltage range (see Note 5)		-0.2 to 4	-0.3 to 4.2		-0.2 to 4	-0.3 to 4.2		-0.2 to 4	-0.3 to 4.2		V
Vон	High-level output voltage	V _{ID} = 100 mV, R _L †	3.2	3.8		3.2	3.9		3.2	4.1		V
VOL	Low-level output voltage	$V_{ID} = -100 \text{ mV},$ $I_{OL} = 0$		0	50		0	50		0	50	mV
A _{VD}	Large-signal differential voltage amplification	V _O = 0.25 V, R _L †	5	23		25	170		50	480		V/mV
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICR} min	65	80		65	91		65	94		dB
ksvr	Supply-voltage rejection ratio ($\Delta V_{DD}/\Delta V_{IO}$)	V _{DD} = 5 V to 10 V, V _O = 1.4 V	65	95		70	93		70	97		dB
I _I (SEL)	Input current (BIAS SELECT)	V _{I(SEL)} = V _{DD} /2		-1.4			-0.13			0.065		μΑ
IDD	Supply current	$V_O = V_{DD}/2,$ $V_{IC} = V_{DD}/2,$ No load		675	1600		105	280		10	17	μΑ

† For high-bias mode, $R_L = 10 \text{ k}\Omega$; for medium-bias mode, $R_L = 100 \text{ k}\Omega$; and for low-bias mode, $R_L = 1 \text{ M}\Omega$. NOTES: 4. The typical values of input bias current and input offset current below 5 pA were determined mathematically. 5. This range also applies to each input individually.

operating characteristics, V_{DD} = 5 V, T_A = 25°C

					TLC251Y								
PARAMETER		TEST CONDITIONS		HIGH-BIAS MODE		MEDIUM-BIAS MODE			LOW-BIAS MODE			UNIT	
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
SR	Slew rate at	RL [†] ,	V _{I(PP)} = 1 V		3.6			0.43			0.03		V/μs
J SK	unity gain	$C_L = 20 pF$	$V_{I(PP)} = 2.5 \text{ V}$		2.9			0.40			0.03		ν/μ5
Vn	Equivalent input noise voltage	f = 1 kHz,	R _S = 20 Ω		25			32			68		nV/√ Hz
ВОМ	Maximum output swing bandwidth	$V_O = V_{OH}$, $R_L = 10 \text{ k}\Omega$	$C_L = 20 pF,$		320			55			4.5		kHz
B ₁	Unity-gain bandwidth	V _I = 10 mV,	C _L = 20 pF		1700		·	525	·		65	·	kHz
φm	Phase margin	f = B ₁ , C _L = 20 pF	V _I = 10 mV,		46°		·	40°	·		34°	·	

[†] For high-bias mode, $R_L = 10 \text{ k}\Omega$; for medium-bias mode, $R_L = 100 \text{ k}\Omega$; and for low-bias mode, $R_L = 1 \text{ M}\Omega$.

PARAMETER MEASUREMENT INFORMATION

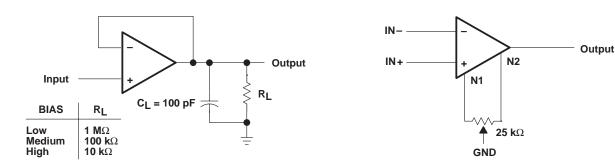


Figure 1. Unity-Gain Amplifier

Figure 2. Input Offset Voltage Null Circuit

TYPICAL CHARACTERISTICS

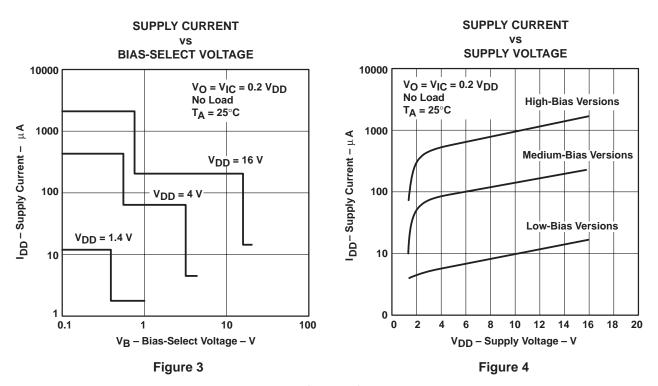
Table of Graphs

IDD	Supply current	vs Bias-select voltage vs Supply voltage vs Free-air temperature	3 4 5						
	Large-signal differential voltage amplification	Low bias	vs Frequency	6					
AVD		Medium bias	vs Frequency	7					
		High bias	vs Frequency	8					
		Low bias	vs Frequency	6					
	Phase shift	Medium bias	vs Frequency	7					
		High bias	vs Frequency	8					



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TYPICAL CHARACTERISTICS



SUPPLY CURRENT VS FREE-AIR TEMPERATURE 10000 $V_{DD} = 10^{1}V$ VIC = 0 VV_O = 2 V **High-Bias Versions** No Load I_{DD} – Supply Current – μ A 1000 **Medium-Bias Versions Low-Bias Versions** 10 30 40 50 60 70 80 T_A - Free-Air Temperature - °C



Figure 5

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TYPICAL CHARACTERISTICS

LOW-BIAS LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT

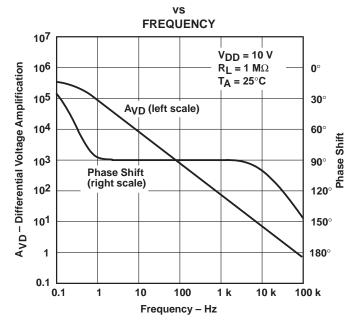


Figure 6

MEDIUM-BIAS LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT

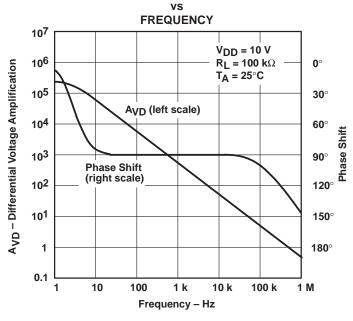


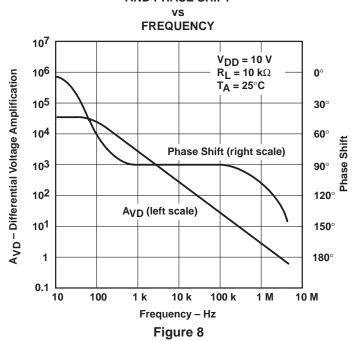
Figure 7



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TYPICAL CHARACTERISTICS

HIGH-BIAS LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT



APPLICATION INFORMATION

latch-up avoidance

Junction-isolated CMOS circuits have an inherent parasitic PNPN structure that can function as an SCR. Under certain conditions, this SCR may be triggered into a low-impedance state, resulting in excessive supply current. To avoid such conditions, no voltage greater than 0.3 V beyond the supply rails should be applied to any pin. In general, the operational amplifier supplies should be applied simultaneously with, or before, application of any input signals.



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APPLICATION INFORMATION

using BIAS SELECT

The TLC251 has a terminal called BIAS SELECT that allows the selection of one of three I_{DD} conditions (10, 150, and 1000 μ A typical). This allows the user to trade-off power and ac performance. As shown in the typical supply current (I_{DD}) versus supply voltage (V_{DD}) curves (Figure 4), the I_{DD} varies only slightly from 4 V to 16 V. Below 4 V, the I_{DD} varies more significantly. Note that the I_{DD} values in the medium- and low-bias modes at $V_{DD} = 1.4$ V are typically 2 μ A, and in the high mode are typically 12 μ A. The following table shows the recommended BIAS SELECT connections at $V_{DD} = 10$ V.

	BIAS MODE	AC PERFORMANCE	BIAS SELECT CONNECTION [†]	TYPICAL I _{DD} ‡
ſ	Low	Low	V_{DD}	10 μΑ
1	Medium	Medium	0.8 V to 9.2 V	150 μΑ
١	High	High	Ground pin	1000 μΑ

[†] Bias selection may also be controlled by external circuitry to conserve power, etc. For information regarding BIAS SELECT, see Figure 3 in the typical characteristics curves.

output stage considerations

The amplifier's output stage consists of a source-follower-connected pullup transistor and an open-drain pulldown transistor. The high-level output voltage (V_{OH}) is virtually independent of the I_{DD} selection and increases with higher values of V_{DD} and reduced output loading. The low-level output voltage (V_{OL}) decreases with reduced output current and higher input common-mode voltage. With no load, V_{OL} is essentially equal to the potential of V_{DD} –/GND.

input offset nulling

The TLC251C series offers external offset null control. Nulling may be achieved by adjusting a 25-k Ω potentiometer connected between the offset null terminals with the wiper connected to the device V_{DD} –/GND pin as shown in Figure 2. The amount of nulling range varies with the bias selection. At an I_{DD} setting of 1000 μ A (high bias), the nulling range allows the maximum offset specified to be trimmed to zero. In low or medium bias or when the amplifier is used below 4 V, total nulling may not be possible for all units.

supply configurations

Even though the TLC251C series is characterized for single-supply operation, it can be used effectively in a split-supply configuration when the input common-mode voltage (V_{ICR}), output swing (V_{OL} and V_{OH}), and supply voltage limits are not exceeded.

circuit layout precautions

The user is cautioned that whenever extremely high circuit impedances are used, care must be exercised in layout, construction, board cleanliness, and supply filtering to avoid hum and noise pickup, as well as excessive dc leakages.



[‡] For I_{DD} characteristics at voltages other than 10 V, see Figure 4 in the typical characteristics curves.

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